

PNP HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/433

Devices

2N4399

2N5745

Qualified Level

**JANTX
JANTXV**

MAXIMUM RATINGS

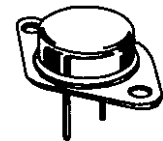
Ratings	Symbol	2N4399	2N5745	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CBO}	60	80	Vdc
Emitter-Base Voltage	V_{EBO}		5.0	Vdc
Base Current	I_B		7.5	Adc
Collector Current	I_C	30	20	Adc
Total Power Dissipation	P_T	@ $T_A = +25^{\circ}C$ (1)	5.0	W
		@ $T_C = +100^{\circ}C$ (2)	115	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-55 to +200		$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.875	$^{\circ}C/W$
Junction-to-Ambient	$R_{\theta JA}$	35	

1) Derate linearly @ 28.57 mW/ $^{\circ}C$ for $T_A > +25^{\circ}C$

2) Derate linearly @ 1.15 W/ $^{\circ}C$ for $T_C > +100^{\circ}C$



TO-3*
(TO-204AA)

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 200$ mAdc	2N4399 2N5745	$V_{(BR)CEO}$	60 80	Vdc
Collector-Emitter Cutoff Current $V_{CE} = 60$ Vdc	2N4399	I_{CEO}	100	μ Adc
$V_{CE} = 80$ Vdc	2N5745		100	
Collector-Emitter Cutoff Current $V_{CE} = 60$ Vdc, $V_{BE} = 1.5$ Vdc	2N4399	I_{CEX}	5.0	μ Adc
$V_{CE} = 80$ Vdc, $V_{BE} = 1.5$ Vdc	2N5745		5.0	
Emitter-Base Cutoff Current $V_{EB} = 5.0$ Vdc		I_{EBO}	5.0	μ Adc

2N4399, 2N5745 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽³⁾				
Forward-Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 2.0 Vdc I _C = 15 Adc, V _{CE} = 2.0 Vdc I _C = 10 Adc, V _{CE} = 2.0 Vdc I _C = 30 Adc, V _{CE} = 5.0 Vdc I _C = 20 Adc, V _{CE} = 5.0 Vdc	h _{FE}	40 15 15 5.0 5.0	425 60 60	
Collector-Emitter Saturation Voltage I _C = 5.0 Adc, I _B = 0.5 Adc I _C = 10 Adc, I _B = 1.0 Adc	V _{CE(sat)}		0.55 0.75 1.0	Vdc
Base-Emitter Saturation Voltage I _C = 10 Adc, I _B = 1.0 Adc I _C = 15 Adc, I _B = 1.5 Adc	V _{BE(sat)}		1.7 1.8 2.0	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz	h _{fe}	4.0	40	
Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 1.0 Adc, V _{CE} = 10 Vdc, f = 1.0 MHz	h _{fe}	40	425	
Output Capacitance V _{CB} = 10 Vdc, I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}		1000	pF

SAFE OPERATING AREA

DC Tests T _C = +25°C, 1 Cycle, t = 1.0 s				
Test 1 V _{CE} = 6.67 Vdc, I _C = 30 Adc V _{CE} = 10 Vdc, I _C = 20 Adc				
Test 2 V _{CE} = 20 Vdc, I _C = 10 Adc				
Test 3 V _{CE} = 40 Vdc, I _C = 3.0 Adc				
Test 4 V _{CE} = 50 Vdc, I _C = 600 mA V _{CE} = 60 Vdc, I _C = 600 mA				

(3) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.